

SANYO

No.2819A

SVC351,361

Diffused Junction Type Silicon Diode

Composite Varactor Diode for AM Receiver Electronic Tuning Use

Features

- Excellent matching characteristics because of composite type
- The number of manufacturing processes can be reduced and automatic mounting is possible because of composite type.
- High capacitance ratio and high quality factor

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Reverse Voltage	V_R	-10	V
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

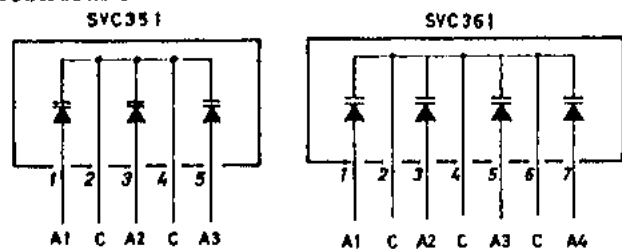
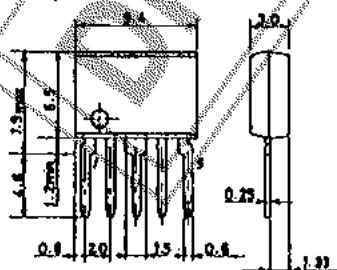
			min	typ	max	unit
Breakdown Voltage	$V_{(BR)R}$	$I_R = -10\mu\text{A}$	-16			V
Reverse Current (One diode)	I_R	$V_R = -9\text{V}$			-100	nA
Interterminal Capacitance (Average)	C_{1V}	$V_R = -1\text{V}, f = 1\text{MHz}^*1$	428.0*		500.0*	pF
	C_{6V}	$V_R = -6\text{V}, f = 1\text{MHz}$	48.0		65.0	pF
	C_{8V}	$V_R = -8\text{V}, f = 1\text{MHz}$	20.5		27.0	pF
Quality Factor	Q	$V_R = -1\text{V}, f = 1\text{MHz}$	200			
Capacitance Ratio	CR	$C_{1V}/C_{8V}, f = 1\text{MHz}$	16.5		23.5	
Matching Tolerance	ΔC_m^*2	$V_R = -1\text{ to } -8\text{V}, f = 1\text{MHz}$			± 2.5	%

*1. 1MHz signal : 20mVrms

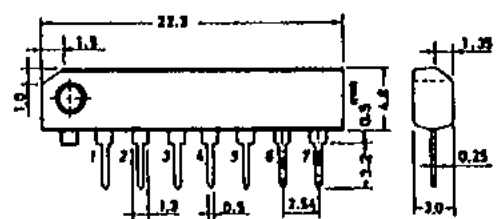
*2. $\Delta C_m = (C_{Dn} - C_{D3})/C_{D3} \times 100$ ※ : The SVC351,361 are classified by C_{1V} as follows :

Rank	C_{1V} (pF)
K	428.0~456.5
L	447.5~478.0
M	468.5~500.0

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced. The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use, nor for any infringements of patents or other rights of third parties which may result from its use.

Electrical Connection**Case Outline 1194 [SVC351]**
(unit : mm)

SANYO : SEP5

Case Outline 1204 [SVC361]
(unit : mm)

SANYO : SEP8

Specifications and information herein are subject to change without notice.

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